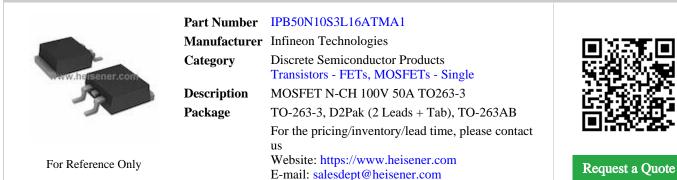


IPB50N10S3L16ATMA1

IPB50N10S3L16ATMA1 Information



Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



IPB50N10S3L16ATMA1 Specifications

Manufacturer Part Number	IPB50N10S3L16ATMA1
Manufacturer	Infineon Technologies
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
Series	OptiMOS?
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	100V
Current - Continuous Drain (Id) @ 25°C	50A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Vgs(th) (Max) @ Id	2.4V @ 60µA
Gate Charge (Qg) (Max) @ Vgs	64nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	4180pF @ 25V
Vgs (Max)	±20V
FET Feature	-
Power Dissipation (Max)	100W (Tc)
Rds On (Max) @ Id, Vgs	15.4 mOhm @ 50A, 10V
Operating Temperature	-55°C ~ 175°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	PG-TO263-3-2
Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
	Report errors?

IPB50N10S3L16ATMA1 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

DISCOVER

IPB50N10S3L16ATMA1 Payment Methods





IPB50N10S3L16ATMA1 Shipping Methods



If you have any question about IPB50N10S3L16ATMA1, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com